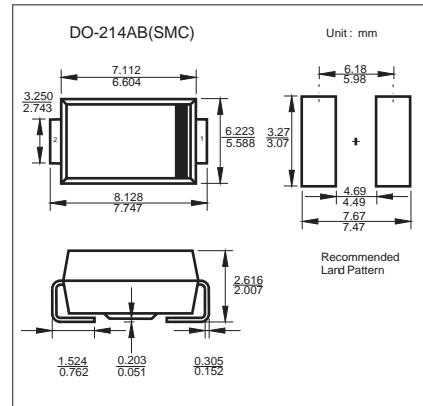


Schottky Diodes

SS32 ~ SS320

■ Features

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications



■ Absolute Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

| Parameter | Symbol | SS 32 | SS 33 | SS 34 | SS 35 | SS 36 | SS 38 | SS 310 | SS 315 | SS 320 | Unit | |
|---|------------|------------|----------|----------|------------|----------|----------|------------|-----------|---------------------------|------------------|--|
| Repetitive Peak Reverse Voltage | V_{RRM} | 20 | 30 | 40 | 50 | 60 | 80 | 100 | 150 | 200 | V | |
| Maximum RMS voltage | V_{RMS} | 14 | 21 | 28 | 35 | 42 | 56 | 70 | 105 | 140 | | |
| Maximum DC Blocking Voltage | V_{DC} | 20 | 30 | 40 | 50 | 60 | 80 | 100 | 150 | 200 | | |
| Maximum average forward rectified current at TL (see fig.1) | $I_{(AV)}$ | 3.0 | | | | | | | | | A | |
| Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) | I_{FSM} | 70.0 | | | | | | | | | | |
| Instantaneous Forward Voltage at 3A | V_F | 0.55 | | 0.70 | | 0.85 | | 0.95 | | V | | |
| Maximum DC Reverse Current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$ | I_R | 0.5 | | | | 1 | | | | mA | | |
| Typical Junction Capacitance *1 | C_j | 500 | | 300 | | 300 | | 300 | | pF | | |
| Typical thermal resistance *2 | R_{thJA} | 55 | | | | 62 | | | | $^\circ\text{C}/\text{W}$ | | |
| Operating junction temperature range | T_j | -65 to 125 | | | -65 to 150 | | | -65 to 150 | | | $^\circ\text{C}$ | |
| Storage Temperature range | T_{stg} | -65 to 150 | | | | | | | | | | |

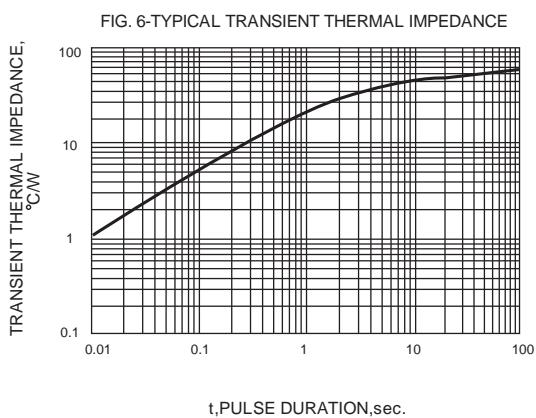
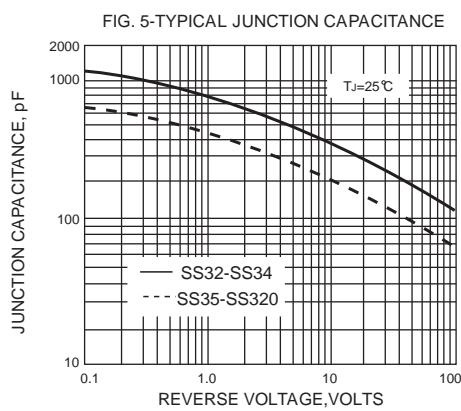
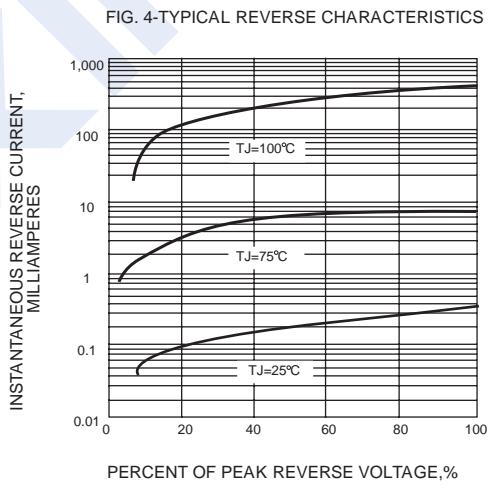
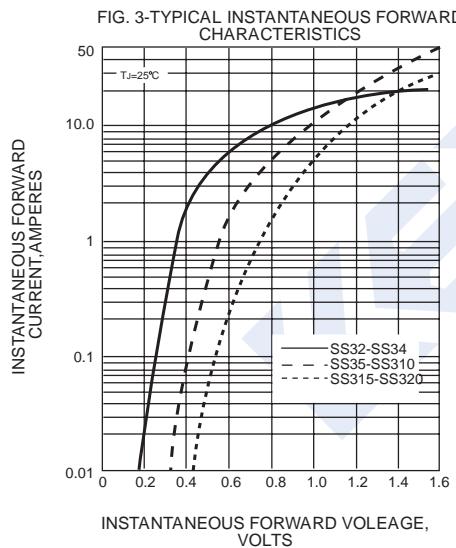
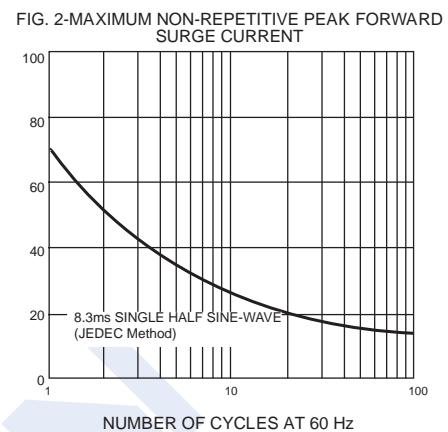
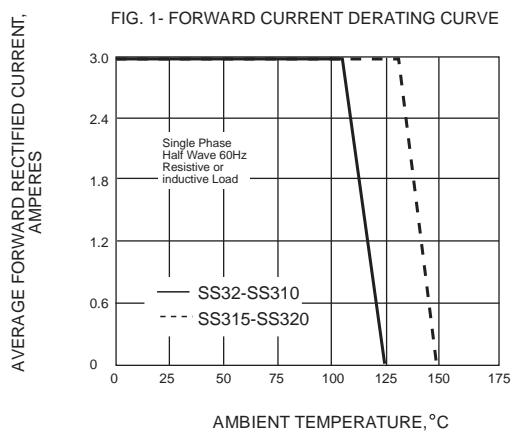
* 1 Measured at 1MHz and applied reverse voltage of 4V D.C

* 2 P.C.B. mounted with 2" x 2" (5x5 cm) copper pad areas.

Schottky Diodes

SS32 ~ SS320

■ Typical Characteristics



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